PEMH20; PUMH20

NPN/NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 04 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN resistor-equipped transistors.

Table 1. Product overview

Type number	ber Package I		NPN/PNP	PNP/PNP
	NXP	JEITA	complement	complement
PEMH20	SOT666	-	PEMD20	PEMB20
PUMH20	SOT363	SC-88	PUMD20	PUMB20

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. Pinning

Table 3.	rinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			sym063

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMH20	-	plastic surface mounted package; 6 leads	SOT666	
PUMH20	SC-88	plastic surface mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH20	6K
PUMH20	H7*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

3 of 9

NPN/NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+12	V
	negative		-	-10	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		[1] -	200	mW
	SOT666		[1][2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2]	300	mW

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
istor					
thermal resistance from junction to ambient	in free air				
SOT363		[1] -	-	625	K/W
SOT666		[1][2] _	-	625	K/W
e					
thermal resistance from junction to ambient	in free air				
SOT363		<u>[1]</u> _	-	416	K/W
SOT666		[1][2]	-	416	K/W
	thermal resistance from junction to ambient SOT363 SOT666 te thermal resistance from junction to ambient SOT363	thermal resistance from in free air junction to ambient SOT363 SOT666 te thermal resistance from in free air junction to ambient SOT363	thermal resistance from in free air junction to ambient SOT363 SOT666 [1] - te thermal resistance from in free air junction to ambient SOT363 [1] -	thermal resistance from in free air junction to ambient SOT363 SOT666 11 2	thermal resistance from in free air junction to ambient SOT363 SOT666 SOT6666 SOT6666

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

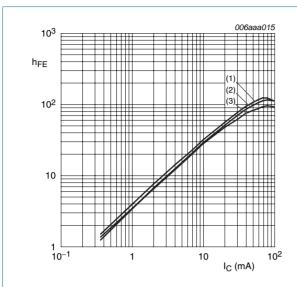
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	2	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_C = 1 \text{ mA}$	-	1.2	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2	1.6	-	V
R1	bias resistor1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF

^[2] Reflow soldering is the only recommended soldering method.



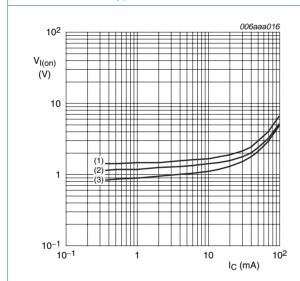
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



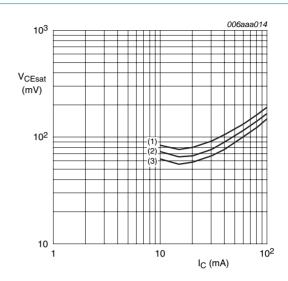
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



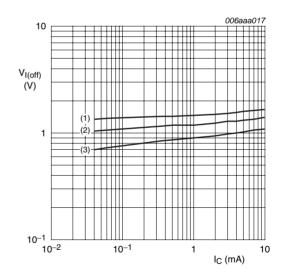
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

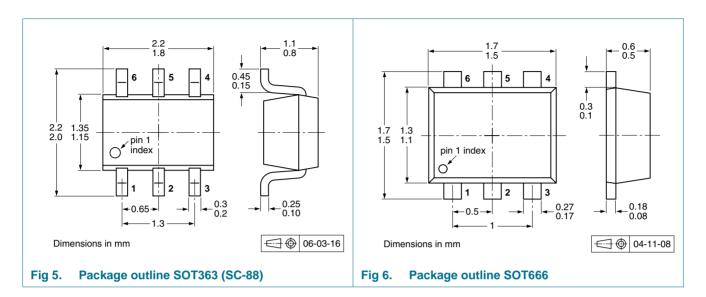
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Package		Description	Packing quantity				
			3000	4000	8000	10000	
PEMH20	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-	-115	-	-	
PUMH20	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165	

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

7 of 9

NPN/NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

10. Revision history

Table 10. Revision history

Product data sheet

Document IDRelease dateData sheet statusChange noticeSupersedesPEMH20_PUMH20_420091115Product data sheet-PEMH20_PUMH20_3Modifications:• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.• Figure 5 "Package outline SOT363 (SC-88)": updatedPEMH20_PUMH20_320050214Product data sheet-PUMH20_2PUMH20_220040414Product specification-PUMH20_1PUMH20_120031016Product specification		•			
Modifications: • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 5 "Package outline SOT363 (SC-88)": updated PEMH20_PUMH20_3 20050214 Product data sheet - PUMH20_2 PUMH20_2 20040414 Product specification - PUMH20_1	Document ID	Release date	Data sheet status	Change notice	Supersedes
including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 5 "Package outline SOT363 (SC-88)": updated PEMH20_PUMH20_3 20050214 Product data sheet - PUMH20_2 PUMH20_2 20040414 Product specification - PUMH20_1	PEMH20_PUMH20_4	20091115	Product data sheet	-	PEMH20_PUMH20_3
PUMH20_2 20040414 Product specification - PUMH20_1	Modifications:	including new legal definitions and disclaimers. No changes were made to the technical content.			
- '	PEMH20_PUMH20_3	20050214	Product data sheet	-	PUMH20_2
PUMH20_1 20031016 Product specification	PUMH20_2	20040414	Product specification	-	PUMH20_1
	PUMH20_1	20031016	Product specification	-	-

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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13. Contents

1	Product profile
1.1	General description 1
1.2	Features
1.3	Applications
1.4	Quick reference data 1
2	Pinning information
3	Ordering information
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics4
8	Package outline 6
9	Packing information 6
10	Revision history 7
11	Legal information 8
11.1	Data sheet status
11.2	Definitions 8
11.3	Disclaimers
11.4	Trademarks 8
12	Contact information 8
13	Contents

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